

74HC109; 74HCT109

Dual $\overline{\text{JK}}$ flip-flop with set and reset; positive-edge-trigger

Rev. 3 — 1 August 2016

Product data sheet

1. General description

The 74HC109; 74HCT109 is a dual positive edge triggered $\overline{\text{JK}}$ flip-flop featuring individual nJ and $\text{n}\overline{\text{K}}$ inputs. It has clock (nCP) inputs, set ($\text{n}\overline{\text{SD}}$) and reset ($\text{n}\overline{\text{RD}}$) inputs and complementary nQ and $\text{n}\overline{\text{Q}}$ outputs. The set and reset are asynchronous active LOW inputs and operate independently of the clock input. The nJ and $\text{n}\overline{\text{K}}$ inputs control the state changes of the flip-flops as described in the mode select function table. The nJ and $\text{n}\overline{\text{K}}$ inputs must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation. The $\overline{\text{JK}}$ design allows operation as a D-type flip-flop by connecting the nJ and $\text{n}\overline{\text{K}}$ inputs together. Inputs include clamp diodes. It enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.

2. Features and benefits

- Input levels:
 - ◆ For 74HC109: CMOS level
 - ◆ For 74HCT109: TTL level
- J and $\overline{\text{K}}$ inputs for easy D-type flip-flop
- Toggle flip-flop or “do nothing” mode
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

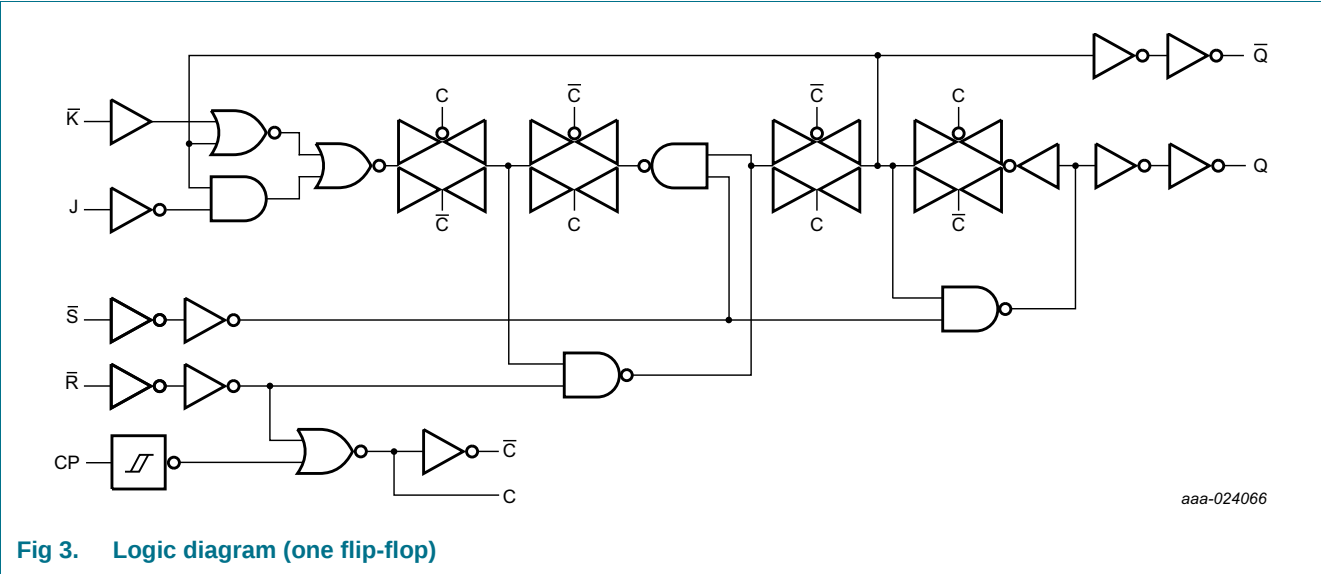
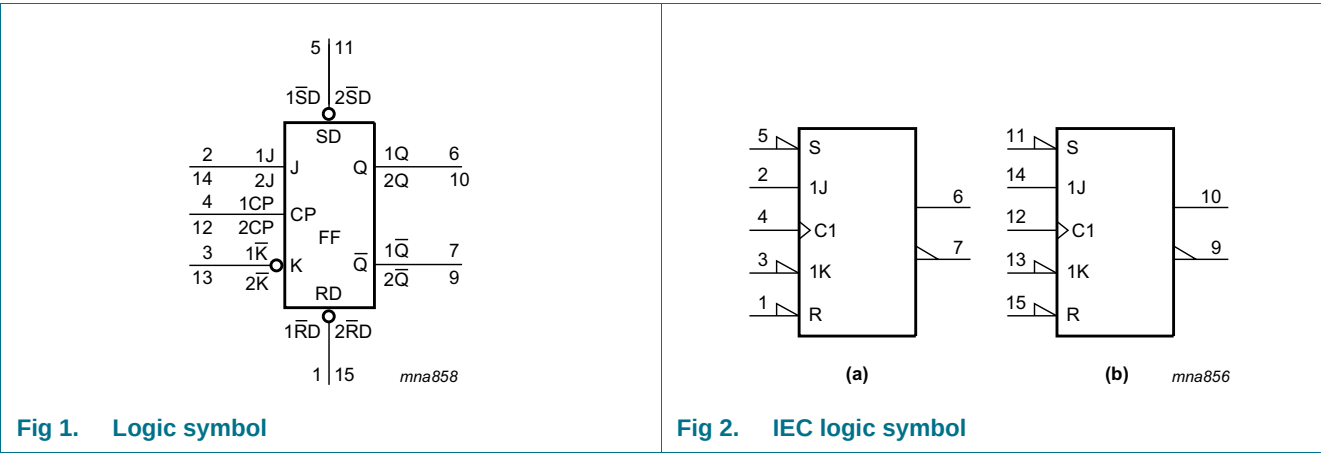


3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC109D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT109D				
74HC109DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT109DB				
74HCT109PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram



5. Pinning information

5.1 Pinning

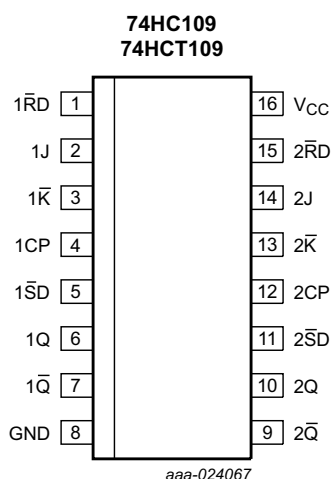


Fig 4. Pin configuration for SO16

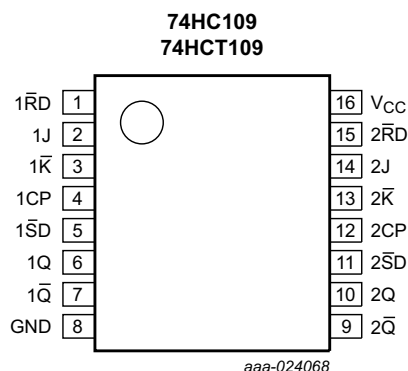


Fig 5. Pin configuration for (T)SSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1RD, 2RD	1, 15	asynchronous reset input (active LOW)
1J, 2J	2, 14	synchronous input
1K, 2K	3, 13	synchronous input
1CP, 2CP	4, 12	clock input (LOW-to-HIGH; edge-triggered)
1SD, 2SD	5, 11	asynchronous set input (active LOW)
1Q, 2Q	6, 10	true flip-flop output
1Q-bar, 2Q-bar	7, 9	complement flip-flop output
GND	8	ground (0 V)
VCC	16	supply voltage

6. Functional description

Table 3. Function selection^[1]

Operating modes	Input					Output	
	nSD	nRD	nCP	nJ	nK	nQ	nQ
Asynchronous set	L	H	X	X	X	H	L
Asynchronous reset	H	L	X	X	X	L	H
Undetermined	L	L	X	X	X	H	H
Toggle	H	H	↑	h	l	$\bar{q}$	q
Load 0 (reset)	H	H	↑	l	l	L	H
Load 1 (set)	H	H	↑	h	h	H	L
Hold no change	H	H	↑	l	h	q	$\bar{q}$

[1] H = HIGH voltage level

h = HIGH voltage level one set-up time before the LOW-to-HIGH CP transition

L = LOW voltage level

l = LOW voltage level one set-up time before the LOW-to-HIGH CP transition

q = lower case letters indicate the state of the referenced output one set-up time before the LOW-to-HIGH CP transition

X = don't care

↑ = LOW-to-HIGH CP transition

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±25	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	SO16 and (T)SSOP16 packages ^[1]	-	500	mW

[1] For SO16 packages: above 70 °C, the value of P_{tot} derates linearly with 8 mW/K.

For (T)SSOP16 packages: above 60 °C, the value of P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC109			74HCT109			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC109										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = −4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = −5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	4.0	-	40	-	80	μA

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT109										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 5.2 mA; V _{CC} = 5.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1	-	±1	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V								
		nJ, nK̄, nSD̄, nRD̄ and nCP inputs	-	35	126	-	157.5	-	171.5	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74HC109										
t _{pd}	propagation delay	nCP to nQ, nQ̄; see Figure 6 ^[2]								
		V _{CC} = 2.0 V	-	50	175	-	220	-	265	ns
		V _{CC} = 4.5 V	-	18	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	30	-	37	-	45	ns
t _{PLH}	LOW to HIGH propagation delay	nSD to nQ, see Figure 7								
		V _{CC} = 2.0 V	-	30	120	-	150	-	180	ns
		V _{CC} = 4.5 V	-	11	24	-	30	-	36	ns
		V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	9	20	-	26	-	31	ns
t _{PHL}	HIGH to LOW propagation delay	nSD to nQ̄; see Figure 7								
		V _{CC} = 2.0 V	-	41	155	-	195	-	235	ns
		V _{CC} = 4.5 V	-	15	31	-	39	-	47	ns
		V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	12	26	-	33	-	40	ns
t _{PHL}	HIGH to LOW propagation delay	nRD to nQ; see Figure 7								
		V _{CC} = 2.0 V	-	41	185	-	230	-	280	ns
		V _{CC} = 4.5 V	-	15	37	-	46	-	56	ns
		V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	12	31	-	39	-	48	ns
t _{PLH}	LOW to HIGH propagation delay	nRD to nQ̄; see Figure 7								
		V _{CC} = 2.0 V	-	39	170	-	215	-	255	ns
		V _{CC} = 4.5 V	-	14	34	-	43	-	51	ns
		V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	11	29	-	37	-	43	ns
t _t	transition time	nQ, nQ̄; see Figure 6 ^[3]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
t_w	pulse width	nCP HIGH or LOW; see Figure 6								
		$V_{CC} = 2.0$ V	80	19	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	7	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	6	-	17	-	20	-	ns
		nSD, nRD HIGH or LOW; see Figure 7								
		$V_{CC} = 2.0$ V	80	14	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	5	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	4	-	17	-	20	-	ns
t_{rec}	recovery time	nSD, nRD to nCP; see Figure 7								
		$V_{CC} = 2.0$ V	70	19	-	90	-	105	-	ns
		$V_{CC} = 4.5$ V	14	7	-	18	-	21	-	ns
		$V_{CC} = 6.0$ V	12	6	-	15	-	18	-	ns
t_{su}	set-up time	nJ and nK to nCP; see Figure 6								
		$V_{CC} = 2.0$ V	70	17	-	90	-	105	-	ns
		$V_{CC} = 4.5$ V	14	6	-	18	-	21	-	ns
		$V_{CC} = 6.0$ V	12	5	-	15	-	18	-	ns
t_h	hold time	nJ and nK to nCP; see Figure 6								
		$V_{CC} = 2.0$ V	5	0	-	5	-	5	-	ns
		$V_{CC} = 4.5$ V	5	0	-	5	-	5	-	ns
		$V_{CC} = 6.0$ V	5	0	-	5	-	5	-	ns
f_{max}	maximum frequency	nCP; see Figure 6								
		$V_{CC} = 2.0$ V	6	22	-	5	-	4	-	MHz
		$V_{CC} = 4.5$ V	30	68	-	24	-	20	-	MHz
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	75	-	-	-	-	-	MHz
		$V_{CC} = 6.0$ V	35	81	-	28	-	24	-	MHz
C_{PD}	power dissipation capacitance	$C_L = 50$ pF; $f = 1$ MHz; $V_I = \text{GND to } V_{CC}$ ^[4]	-	20	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 8](#).

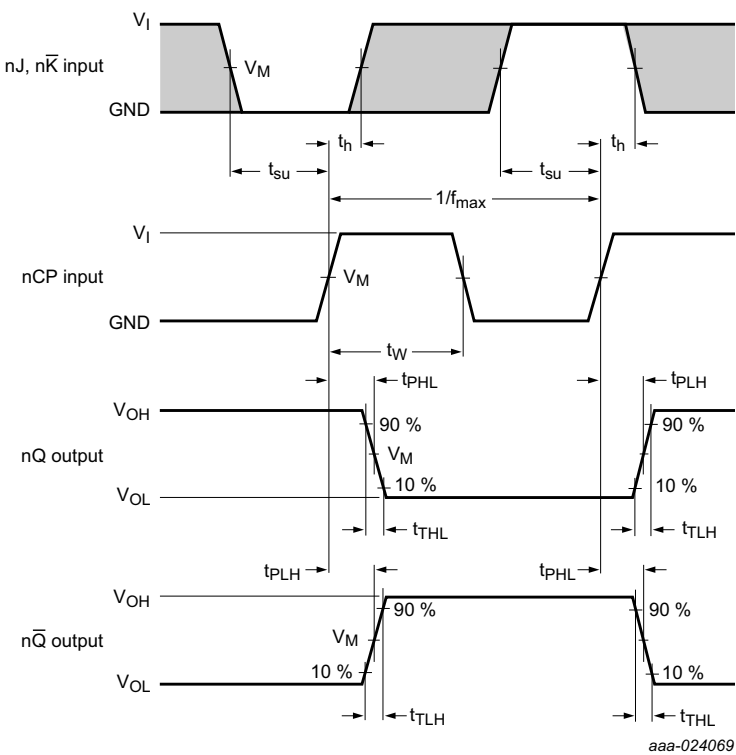
Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74HCT109										
t _{pd}	propagation delay	nCP to nQ, nQ̄; see Figure 6 ^[2]								
		V _{CC} = 4.5 V	-	20	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	17	-	-	-	-	-	ns
t _{PLH}	LOW to HIGH propagation delay	nSD to nQ, see Figure 7								
		V _{CC} = 4.5 V	-	13	26	-	33	-	39	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
t _{PHL}	HIGH to LOW propagation delay	nSD to nQ̄; see Figure 7								
		V _{CC} = 4.5 V	-	19	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
t _{PHL}	HIGH to LOW propagation delay	nRD to nQ; see Figure 7								
		V _{CC} = 4.5 V	-	19	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
t _{PLH}	LOW to HIGH propagation delay	nRD to nQ̄; see Figure 7								
		V _{CC} = 4.5 V	-	16	32	-	40	-	48	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
t _t	transition time	nQ, nQ̄; see Figure 6 ^[3]								
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t _w	pulse width	nCP HIGH or LOW; see Figure 6								
		V _{CC} = 4.5 V	18	9	-	23	-	27	-	ns
		nSD, nRD HIGH or LOW; see Figure 7								
		V _{CC} = 4.5 V	16	8	-	20	-	24	-	ns
t _{rec}	recovery time	nSD, nRD to nCP; see Figure 7								
		V _{CC} = 4.5 V	16	8	-	20	-	24	-	ns
t _{su}	set-up time	nJ and nK̄ to nCP; see Figure 6								
		V _{CC} = 4.5 V	18	8	-	23	-	27	-	ns
t _h	hold time	nJ and nK̄ to nCP; see Figure 6								
		V _{CC} = 4.5 V	3	–3	-	3	-	3	-	ns
f _{max}	maximum frequency	nCP; see Figure 6								
		V _{CC} = 4.5 V	27	55	-	22	-	18	-	MHz
		V _{CC} = 5 V; C _L = 15 pF	-	61	-	-	-	-	-	MHz

Table 7. Dynamic characteristics ...continued
Voltages are referenced to GND (ground = 0 V); $C_L = 50\text{ pF}$ unless otherwise specified; for test circuit, see Figure 8.

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}$; $f = 1\text{ MHz}$; $V_I = \text{GND to } V_{CC} - 1.5\text{ V}$ ^[4]	-	22	-	-	-	-	-	pF

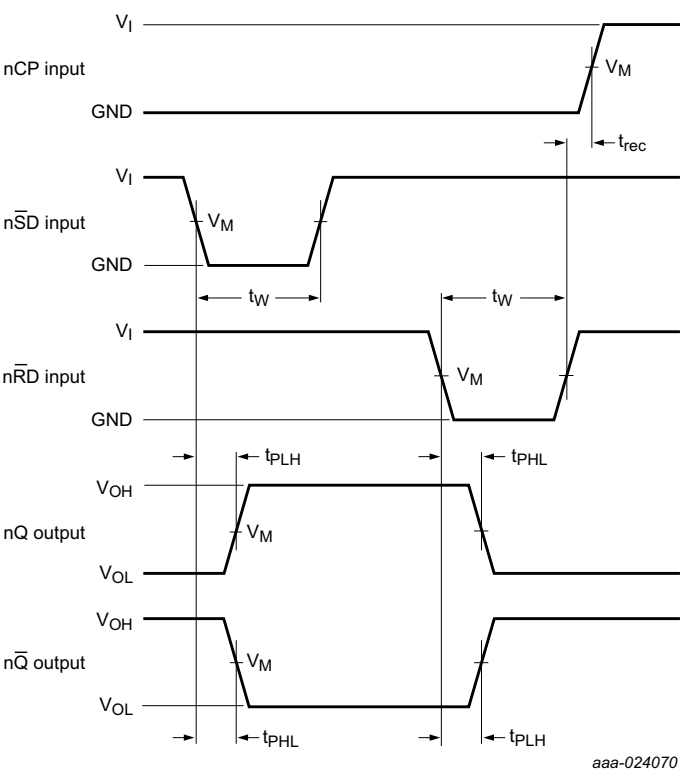
- [1] All typical values are measured at $T_{amb} = 25\text{ °C}$.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] t_t is the same as t_{THL} and t_{TLH} .
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



Measurement points are given in Table 8.
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Clock propagation delays, output transition time, pulse width, set-up, hold times, and maximum frequency

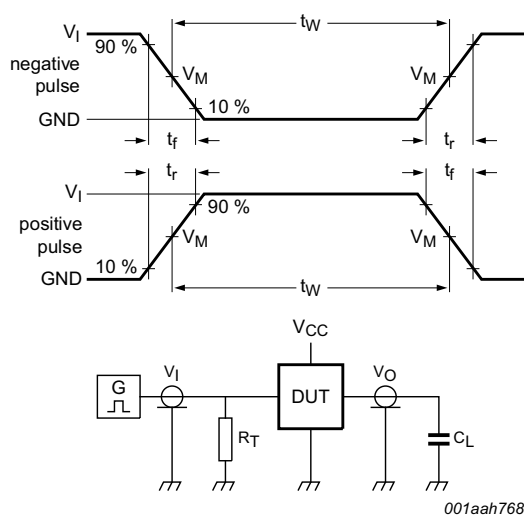


Measurement points are given in [Table 8](#).
V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Set and reset propagation delays, pulse widths and recovery time

Table 8. Measurement points

Type	Input	Output
	V _M	V _M
74HC109	0.5V _{CC}	0.5V _{CC}
74HCT109	1.3 V	1.3 V



Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_l = Load resistance.

Fig 8. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V _I	t _r , t _f	C _L	
74HC109	V _{CC}	6 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT109	3 V	6 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

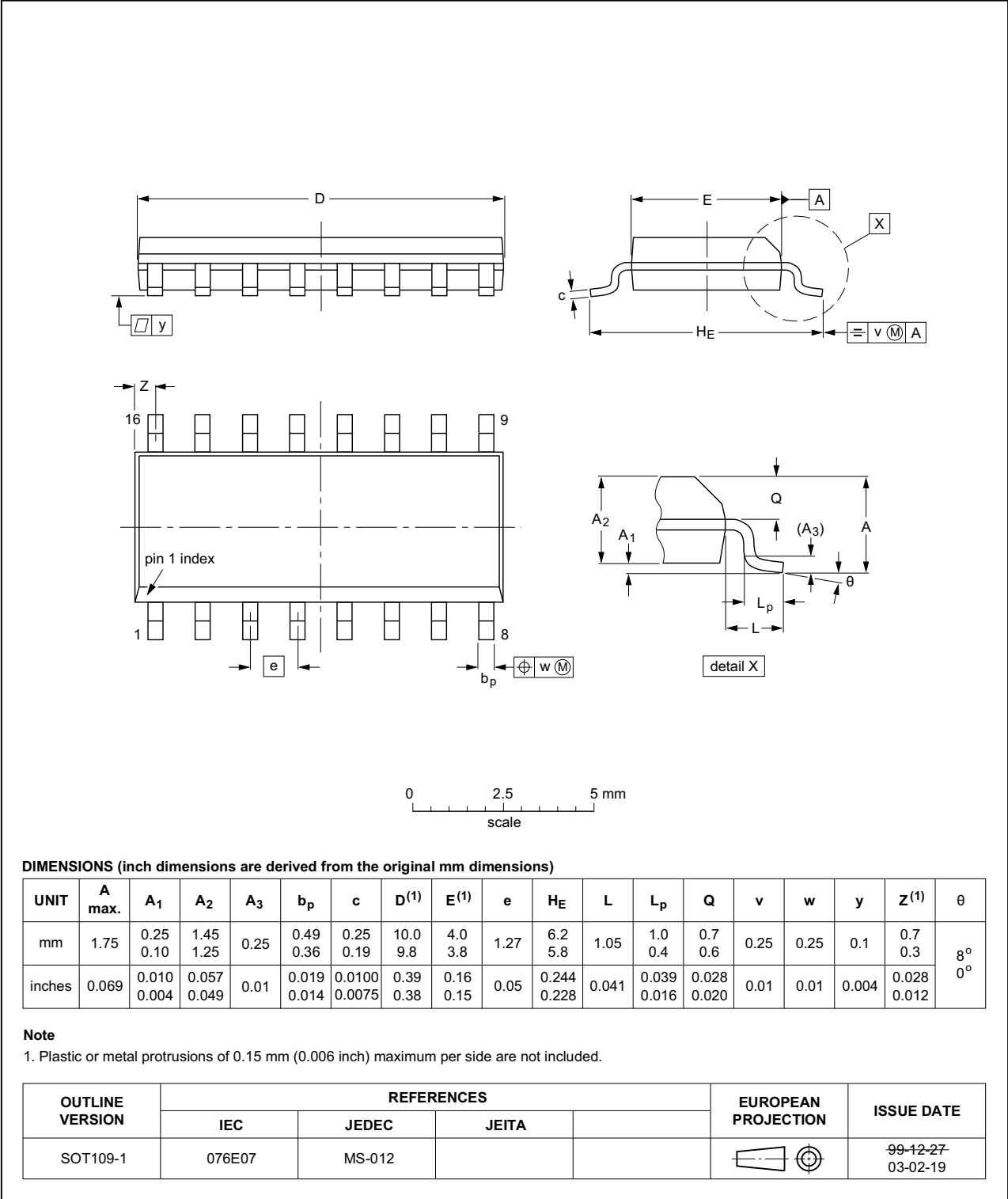


Fig 9. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

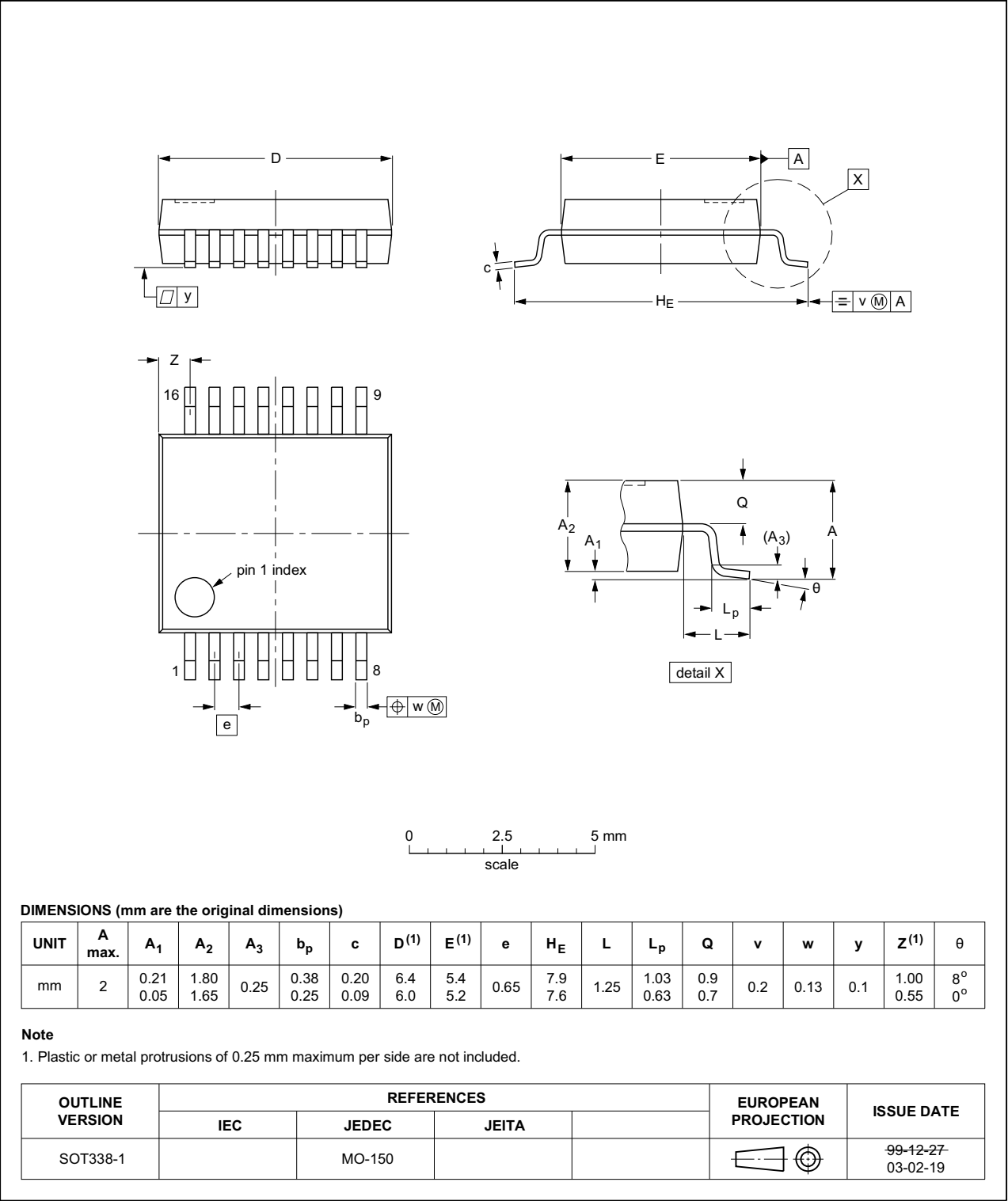


Fig 10. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

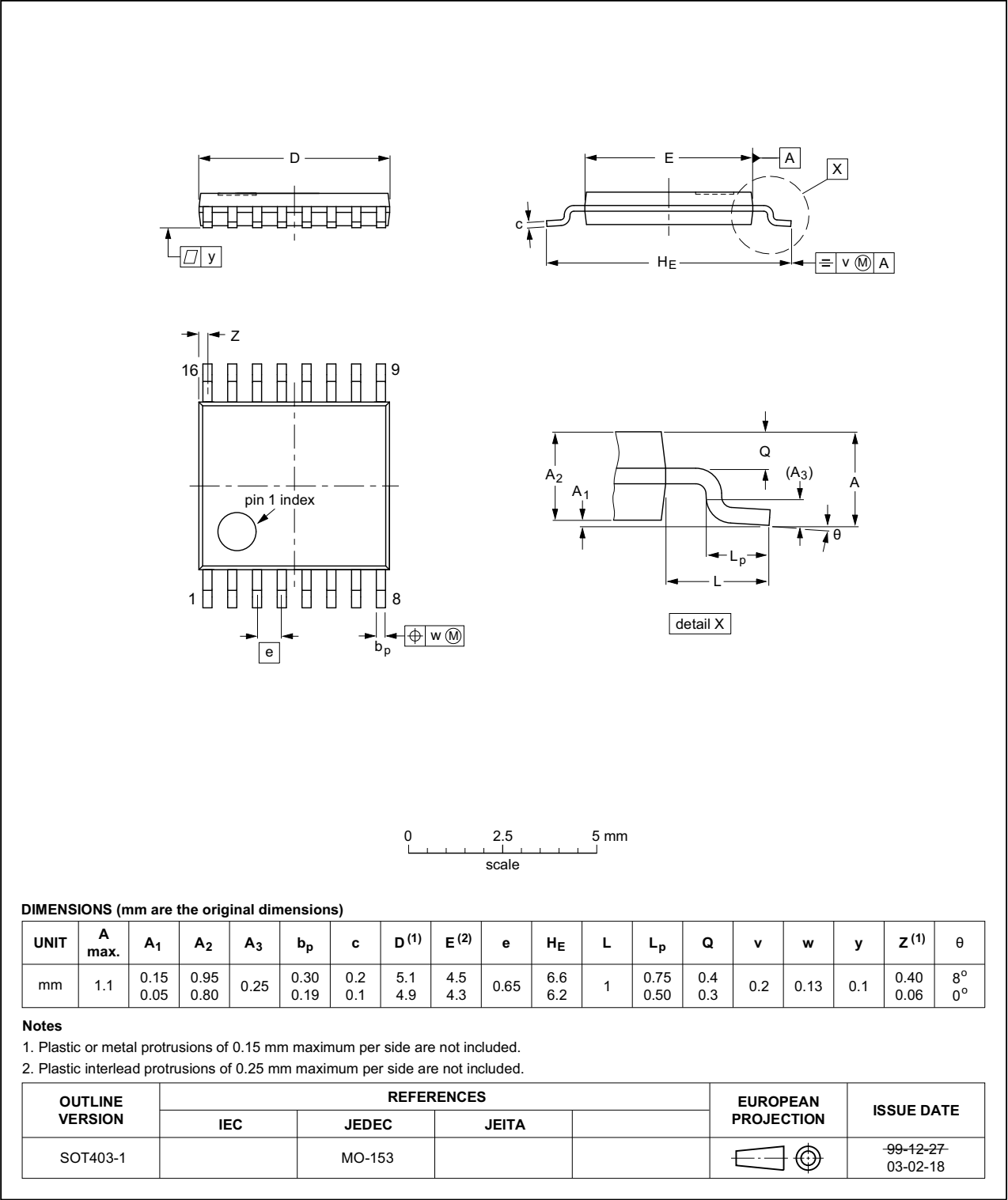


Fig 11. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT109 v.3	20160801	Product data sheet	-	74HC_HCT109_CNV v.2
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT109_CNV v.2	19971125	Product specification	-	-

15. Legal information

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Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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